

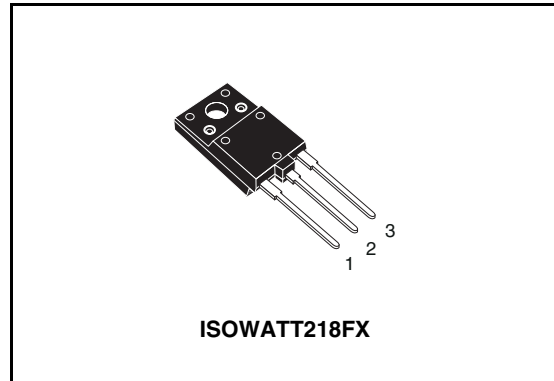


## MD2103DFX

High voltage NPN power transistor for standard definition CRT display

### General features

- State-of-the-art technology:
  - Diffused collector “enhanced generation”
- More stable performance versus operating temperature variation
- Low base drive requirement
- Tighter  $h_{FE}$  range at operating collector current
- Fully insulated power package U.L. compliant
- Integrated free wheeling diode
- In compliance with the 2002/93/EC European Directive



### Description

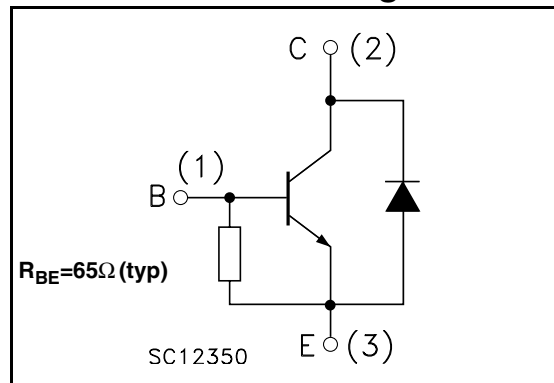
The MD2103DFX is manufactured using Diffused Collector in Planar technology adopting new and enhanced high voltage structure.

The new MD product series show improved silicon efficiency bringing updated performance to the horizontal deflection stage.

### Applications

- Horizontal deflection output for TV

### Internal schematic diagram



### Order codes

Part number	Marking	Package	Packing
MD2103DFX	MD2103DFX	ISOWATT218FX	Tube

## Contents

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# 1 Electrical ratings

**Table 1. Absolute maximum rating**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{BE} = 0$ )	1500	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	700	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	7	V
$I_C$	Collector current	6	A
$I_{CM}$	Collector peak current ( $t_P < 5\text{ms}$ )	9	A
$I_B$	Base current	3	A
$P_{tot}$	Total dissipation at $T_C \leq 25^\circ\text{C}$	52	W
$V_{INS}$	Insulation withstand voltage (RMS) from all three leads to external heatsink	2500	V
$T_{stg}$	Storage temperature	-65 to 150	$^\circ\text{C}$
$T_J$	Max. operating junction temperature	150	$^\circ\text{C}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.4	$^\circ\text{C}/\text{W}$

## 2 Electrical characteristics

( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise specified)

**Table 3. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CES}}$	Collector cut-off current ( $V_{\text{BE}} = 0$ )	$V_{\text{CE}} = 1500\text{V}$ $V_{\text{CE}} = 1500\text{V}$ $T_{\text{C}} = 125^{\circ}\text{C}$			0.2 2	mA mA
$I_{\text{EBO}}$	Emitter cut-off current ( $I_{\text{C}} = 0$ )	$V_{\text{EB}} = 5\text{V}$	50		125	mA
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = 700\text{mA}$		11		V
$V_{\text{CE}(\text{sat})}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 3\text{A}$ $I_{\text{B}} = 0.75\text{A}$			1.8	V
$V_{\text{BE}(\text{sat})}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 3\text{A}$ $I_{\text{B}} = 0.75\text{A}$			1.5	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = 1\text{A}$ $V_{\text{CE}} = 5\text{V}$ $I_{\text{C}} = 3\text{A}$ $V_{\text{CE}} = 1\text{V}$ $I_{\text{C}} = 3\text{A}$ $V_{\text{CE}} = 5\text{V}$	6.5	17 6	9.5	
$t_{\text{s}}$ $t_{\text{f}}$	Inductive load Storage time Fall time	$I_{\text{C}} = 3\text{A}$ $f_{\text{h}} = 16\text{kHz}$ $I_{\text{B}(\text{on})} = 0.5\text{A}$ $V_{\text{BE}(\text{off})} = -2.7\text{V}$ $L_{\text{BB}(\text{off})} = 6.3\mu\text{H}$ (see <a href="#">Figure 9</a> )		3.8 0.25		$\mu\text{s}$ $\mu\text{s}$
$V_{\text{F}}$	Diode forward voltage	$I_{\text{F}} = 3\text{A}$			2	V

Note (1) Pulsed duration = 300  $\mu\text{s}$ , duty cycle  $\leq 5\%$

## 2.1 Electrical cMD2103DFX characteristics (curves)

Figure 1. Safe operating area

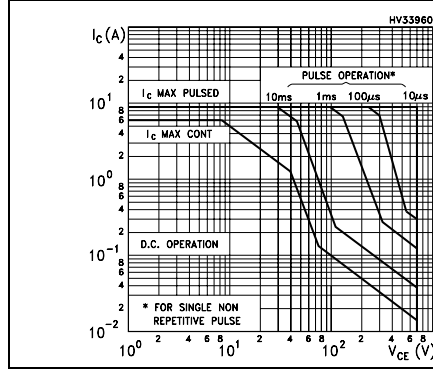


Figure 2. Derating curve

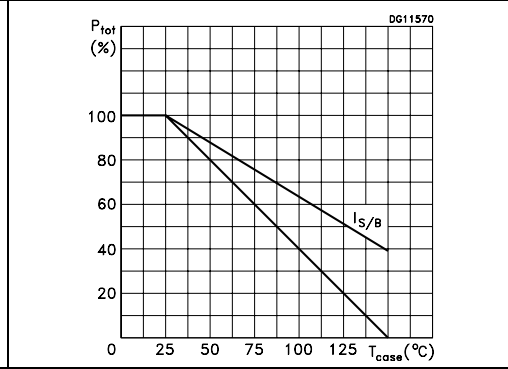


Figure 3. Output characteristics

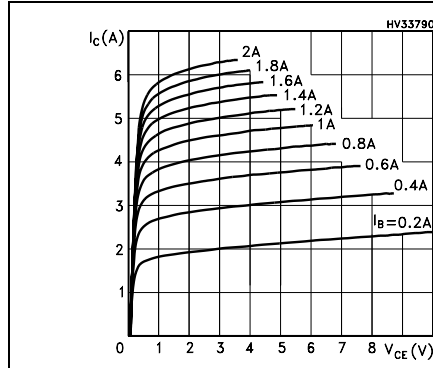


Figure 4. Reverse biased SOA

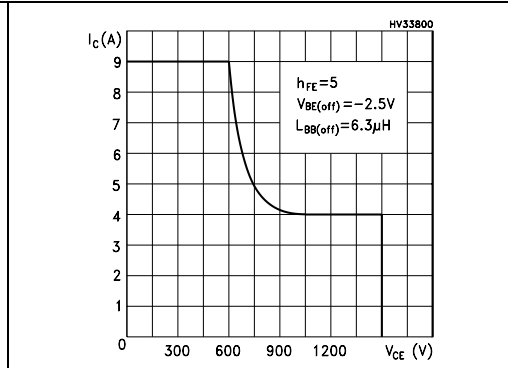


Figure 5. DC current gain

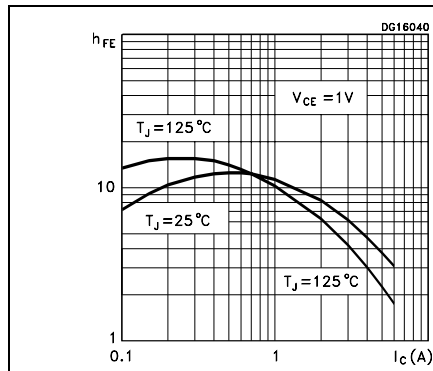
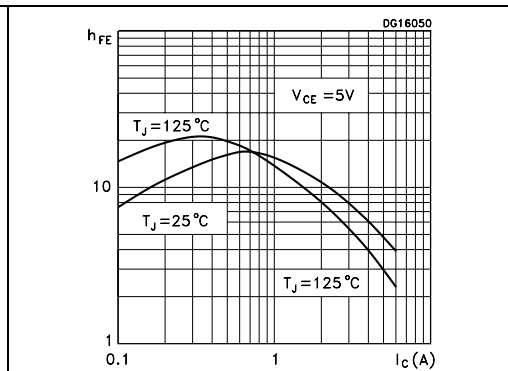
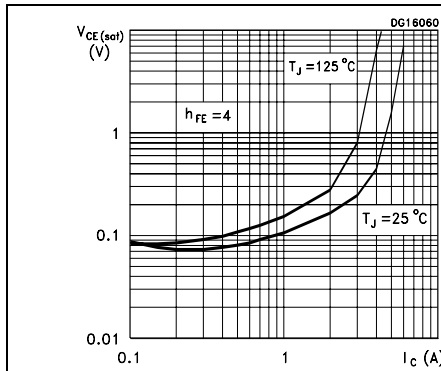


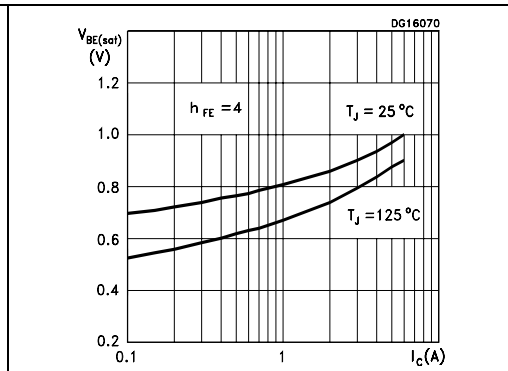
Figure 6. DC current gain



**Figure 7. Collector-emitter saturation voltage**

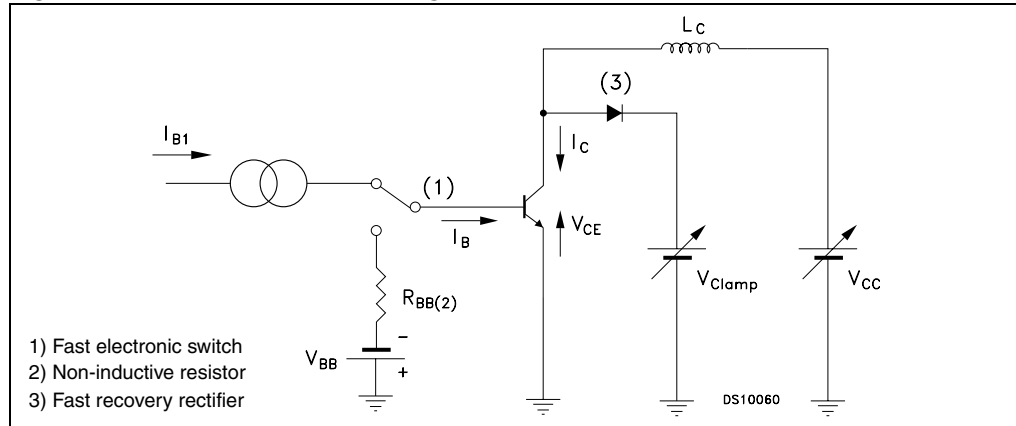


**Figure 8. Base-emitter saturation voltage**



## 2.2 Test circuits

Figure 9. Inductive load switching test circuit



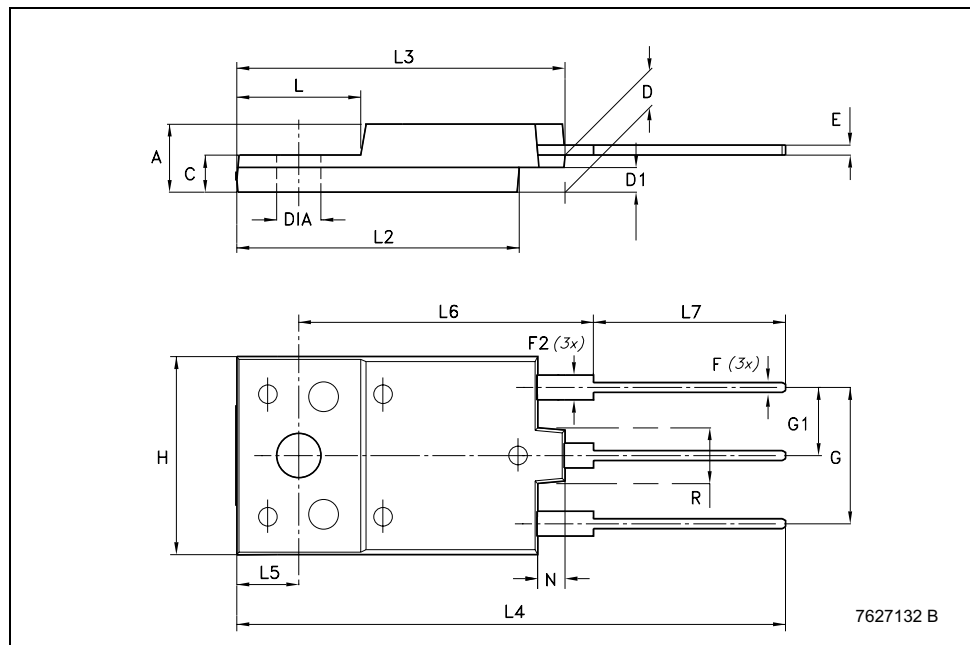
### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)



**ISOWATT218FX MECHANICAL DATA**

DIM.	mm.		
	MIN.	TYP	MAX.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9		10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80



## 4 Revision history

Table 4. Revision history

Date	Revision	Changes
16-Oct-2006	1	First release

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